PE426482

Product Specification

UltraCMOS® SP8T RF Switch, 10 MHz–8 GHz

Features

- High isolation: 41 dB at 6 GHz
- Low insertion loss: 1.1 dB at 6 GHz
- RF T_{RISE}/T_{FALL}: 100 ns
- Power handling: 31 dBm CW
- Logic Select (LS) pin for maximum control logic flexibility
- Terminated all-off state mode
- Operating temperature: –55 °C to +125 °C
- Package: 24-lead 4 × 4 × 0.85 mm QFN

Applications

- Harsh industrial RF switching up to 8 GHz
- Systems requiring extended temperature operation in the –55 °C to +125 °C range
- Filter bank switching
- General RF signal routing

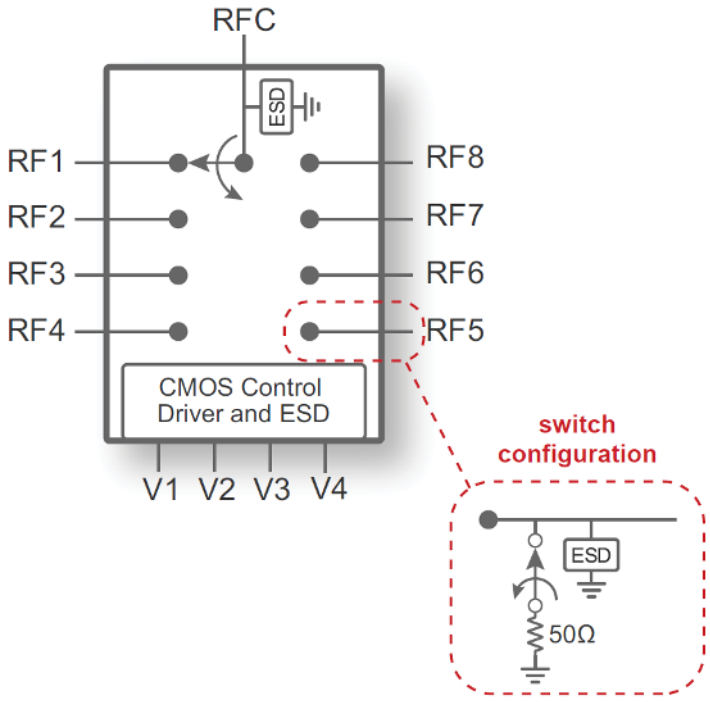


Figure 1: PE426482 functional diagram

Product description

The PE426482 is a HaRP™ technology-enhanced absorptive SP8T RF switch that supports a frequency range from 10 MHz to 8 GHz. It delivers low insertion loss, fast RF T_{RISE}/T_{FALL} time, and high isolation in the operating temperature range from –55 °C to +125 °C. It is ideal for harsh industrial applications that require extended support in this temperature range. No blocking capacitors are required if DC voltage is not present on the RF ports.

The PE426482 is manufactured on pSemi's UltraCMOS® process, a patented advanced form of silicon-on-insulator (SOI) technology.

pSemi's HaRP technology enhancements deliver high linearity and excellent harmonics performance. It is an innovative feature of the UltraCMOS process, offering the performance of GaAs with the economy and integration of conventional CMOS.

Absolute maximum ratings

Exceeding the absolute maximum ratings listed in Table 1 could cause permanent damage. Restrict operation to the limits in Table 2. Operation between the operating range maximum and the absolute maximum for extended periods could reduce reliability.

ESD precautions

When handling this UltraCMOS device, observe the same precautions as with any other ESD-sensitive devices. Although this device contains circuitry to protect it from damage due to ESD, do not exceed the rating listed in Table 1.

Latch-up immunity

Unlike conventional CMOS devices, UltraCMOS devices are immune to latch-up.

Table 1. Absolute maximum ratings

Parameter or condition	Min	Max	Unit
Supply voltage, V_{DD}	–0.3	5.5	V
Digital input voltage (V1, V2, V3, V4, LS)	–0.3	3.6	V
RF input power (RFC–RFx, 50Ω)	–	See Figure 2	dBm
RF input power into terminated ports, CW (RFx, 50Ω)(1)	–	See Figure 2	dBm
Maximum junction temperature	–	+150	°C
Storage temperature range	–65	+150	°C
ESD voltage HBM, all pins(2)	–	1000	V
ESD voltage CDM, all pins(3)	–	1000	V

Notes:
1. 100% duty cycle, all bands, 50Ω
2. Human body model (MIL-STD 883 Method 3015)
3. Charged device model (JEDEC JESD22-C101)

Recommended operating conditions

Table 2 lists the PE426482 recommended operating conditions. Do not operate devices outside the recommended operating conditions listed below.

Table 2. Recommended operating conditions

Parameter	Min	Typ	Max	Unit
Supply voltage, V_{DD}	2.3	3.3	5.5	V
Supply current, I_{DD}	–	120	200	µA
Digital input high (V1, V2, V3, V4, LS)	1.17	–	3.6	V
Digital input low (V1, V2, V3, V4, LS)	–0.3	–	0.6	V
Digital input current (V1, V2, V3, V4)	–	–	5	µA
Digital input current (LS)	–	–	10	µA
RF input power, CW (RFC–RFx)[1]	–	–	See Figure 2	dBm
RF input power, pulsed (RFC–RFx)[2]	–	–	See Figure 2	dBm
RF input power into terminated ports, CW (RFx)[1]	–	–	See Figure 2	dBm
Operating temperature range	–55	+25	+125	°C

Notes:
1. 100% duty cycle, all bands, 50Ω
2. Pulsed 5% duty, 4620-µs period, 50Ω

Electrical specifications

Table 3 lists the PE426482 key electrical specifications at +25 °C, V_{DD} = 3.3V (Z_S = Z_L = 50Ω), unless otherwise specified.

Table 3. Electrical specifications

Parameter	Path	Condition	Min	Typ	Max	Unit
Operating frequency	–	–	10 MHz	–	8 GHz	As shown
Insertion loss[1]	RFC–RF1/8	10–100 MHz 100 MHz–1 GHz 1–2 GHz 2–4 GHz 4–6 GHz 6–8 GHz	–	0.7 0.8 0.9 0.9 1.1 1.6	0.9 1.0 1.2 1.5 1.9 2.8	dB
	RFC–RF2/7	10–100 MHz 100 MHz–1 GHz 1–2 GHz 2–4 GHz 4–6 GHz 6–8 GHz	–	0.8 0.9 0.9 1.0 1.3 1.3	1.0 1.1 1.3 1.6 2.3 2.4	dB
	RFC–RF3/6	10–100 MHz 100 MHz–1 GHz 1–2 GHz 2–4 GHz 4–6 GHz 6–8 GHz	–	0.8 0.9 1.0 1.1 1.2 1.3	1.0 1.1 1.3 1.7 2.2 2.2	dB
	RFC–RF4/5	10–100 MHz 100 MHz–1 GHz 1–2 GHz 2–4 GHz 4–6 GHz 6–8 GHz	–	0.9 1.1 1.2 1.3 1.4 1.5	1.1 1.3 1.6 1.9 2.2 2.8	dB
Isolation[1]	RFC–RF1/8	10–100 MHz 100 MHz–1 GHz 1–2 GHz 2–4 GHz 4–6 GHz 6–8 GHz	61 45 39 34 29 25	65 47 41 36 32 30	–	dB
	RFC–RF2/7	10–100 MHz 100 MHz–1 GHz 1–2 GHz 2–4 GHz 4–6 GHz 6–8 GHz	63 50 45 38 30 29	67 53 47 41 34 34	–	dB
	RFC–RF3/6	10–100 MHz 100 MHz–1 GHz 1–2 GHz 2–4 GHz 4–6 GHz 6–8 GHz	64 51 46 38 33 29	68 53 48 40 35 31	–	dB

Parameter	Path	Condition	Min	Typ	Max	Unit
	RFC–RF4/5	10–100 MHz 100 MHz–1 GHz 1–2 GHz 2–4 GHz 4–6 GHz 6–8 GHz	81 57 50 45 38 33	85 62 56 48 41 38	–	dB
Return loss (active port)	RFC–RF1/8	10–100 MHz 100 MHz–1 GHz 1–2 GHz 2–4 GHz 4–6 GHz 6–8 GHz	–	25 24 24 21 26 13	–	dB
	RFC–RF2/7	10–100 MHz 100 MHz–1 GHz 1–2 GHz 2–4 GHz 4–6 GHz 6–8 GHz	–	24 23 20 18 15 16	–	dB
	RFC–RF3/6	10–100 MHz 100 MHz–1 GHz 1–2 GHz 2–4 GHz 4–6 GHz 6–8 GHz	–	24 23 18 15 12 12	–	dB
	RFC–RF4/5	10–100 MHz 100 MHz–1 GHz 1–2 GHz 2–4 GHz 4–6 GHz 6–8 GHz	–	24 23 17 15 16 18	–	dB
Return loss (RFC port)	RFC–RF1/8	10–100 MHz 100 MHz–1 GHz 1–2 GHz 2–4 GHz 4–6 GHz 6–8 GHz	–	25 23 24 23 24 12	–	dB
	RFC–RF2/7	10–100 MHz 100 MHz–1 GHz 1–2 GHz 2–4 GHz 4–6 GHz 6–8 GHz	–	24 23 21 19 20 18	–	dB
	RFC–RF3/6	10–100 MHz 100 MHz–1 GHz 1–2 GHz 2–4 GHz 4–6 GHz 6–8 GHz	–	24 23 19 16 13 13	–	dB

Parameter	Path	Condition	Min	Typ	Max	Unit
	RFC–RF4/5	10–100 MHz 100 MHz–1 GHz 1–2 GHz 2–4 GHz 4–6 GHz 6–8 GHz	–	24 22 18 16 17 17	–	dB
Return loss (terminated port)	RF1/8	10–100 MHz 100 MHz–1 GHz 1–2 GHz 2–4 GHz 4–6 GHz 6–8 GHz	–	16 15 15 15 18 21	–	dB
	RF2/7	10–100 MHz 100 MHz–1 GHz 1–2 GHz 2–4 GHz 4–6 GHz 6–8 GHz	–	16 15 15 15 18 19	–	dB
	RF3/6	10–100 MHz 100 MHz–1 GHz 1–2 GHz 2–4 GHz 4–6 GHz 6–8 GHz	–	16 15 15 15 16 19	–	dB
	RF4/5	10–100 MHz 100 MHz–1 GHz 1–2 GHz 2–4 GHz 4–6 GHz 6–8 GHz	–	16 15 15 16 23 16	–	dB
Relative insertion phase[2]	RF2–RF1 (RF7–RF8)	1 GHz 2 GHz 4 GHz 6 GHz 8 GHz	–2.6 –4.7 –7.5 –9.4 –1.4	–1.3 –2.4 –3.4 –2.8 4.4	0 –0.1 0.8 3.8 10.1	deg
	RF3–RF1 (RF6–RF8)	1 GHz 2 GHz 4 GHz 6 GHz 8 GHz	–3.0 –5.8 –9.3 –11.2 –10.2	–2.1 –4.0 –5.6 –5.7 –1.0	–1.3 –2.1 –1.9 –0.3 8.2	deg
	RF4–RF1 (RF5–RF8)	1 GHz 2 GHz 4 GHz 6 GHz 8 GHz	–6.9 –13.3 –24.7 –35.8 –45.3	–5.6 –10.7 –18.9 –26.3 –31.5	–4.3 –8.2 –13.0 –16.9 –17.6	deg
Input 1-dB compression point[3]	RFC–RFx	–	–	See Figure 2	–	dBm
Input 0.1-dB compression point[3]	RFC–RFx	–	–	See Figure 2	–	dBm
Input IP2	RFC–RFx	100 MHz–8 GHz	–	105	–	dBm

Parameter	Path	Condition	Min	Typ	Max	Unit
Input IP3	RFC–RFx	100 MHz–8 GHz	–	60	–	dBm
RF T_{RISE}/T_{FALL}	–	10%/90% RF	–	100	130	ns
Settling time	–	50% CTRL to 0.05 dB final value	–	870	1400	ns
Switching time	–	50% CTRL to 90% or 10% of RF	–	227	290	ns

Notes:
1. Insertion loss and isolation performance can be improved by an RF ground on LS (pin 1).
2. Defined with S-parameters, relative insertion phase (RFx–RF1) = ∠S(x+1)1 – ∠S21, where incident Port-1 = RFC, response Port-2 = RF1, and response Port-(x+1) = RFx.
3. The input 1-dB and 0.1-dB compression points are linearity figures of merit. For the RF input power (50Ω), see Table 2.

Switching frequency

The PE426482 has a maximum 25 kHz switching frequency. The switching frequency describes the time duration between switching events. The switching time is the time duration between the point that the control signal reached 50% of the final value and the point that the output signal reaches within 10% or 90% of its target value.

Spurious performance

The PE426482 spur fundamental occurs around 5 MHz. Its typical performance is –162 dBm/Hz, with 30 kHz bandwidth.

Hot-switching capability

The PE426482 maximum hot switching capability is 18 dBm above 100 MHz. Hot switching occurs when RF power is applied while switching between RF ports.

Thermal data

The junction top-of-package, Psi-JT (Ψ_{JT}), is a thermal metric to estimate the junction temperature of the device in an application PCB, per JEDEC JESD51-2:

$$\Psi_{JT} = (T_J - T_T)/P$$

where:

- Ψ_{JT} = Junction-to-top of package characterization parameter in °C/W
- T_J = Die junction temperature in °C
- T_T = Package temperature (top surface, in the center) in °C
- P = Power dissipated by the device in Watts

Table 4. Thermal data

Parameter	Typ	Unit
Junction top-of-package, Ψ_{JT}	23	°C/W
Junction-to-ambient thermal resistance, Θ_{JA}	63	°C/W

Control logic

Table 5 lists the PE426482 control logic truth table.

Table 5. Truth table

LS[1]	V4	V3	V2	V1	RFC–RF1	RFC–RF2	RFC–RF3	RFC–RF4	RFC–RF5	RFC–RF6	RFC–RF7	RFC–RF8
0	0	0	0	0	ON	OFF	OFF	OFF	OFF	OFF	OFF	OFF
0	0	1	0	0	OFF	ON	OFF	OFF	OFF	OFF	OFF	OFF
0	0	0	1	0	OFF	OFF	ON	OFF	OFF	OFF	OFF	OFF
0	0	1	1	0	OFF	OFF	OFF	ON	OFF	OFF	OFF	OFF
0	0	0	0	1	OFF	OFF	OFF	OFF	ON	OFF	OFF	OFF
0	0	1	0	1	OFF	OFF	OFF	OFF	OFF	ON	OFF	OFF
0	0	0	1	1	OFF	OFF	OFF	OFF	OFF	OFF	ON	OFF
0	0	1	1	1	OFF	OFF	OFF	OFF	OFF	OFF	OFF	ON
1	0	1	1	1	ON	OFF	OFF	OFF	OFF	OFF	OFF	OFF
1	0	0	1	1	OFF	ON	OFF	OFF	OFF	OFF	OFF	OFF
1	0	1	0	1	OFF	OFF	ON	OFF	OFF	OFF	OFF	OFF
1	0	0	0	1	OFF	OFF	OFF	ON	OFF	OFF	OFF	OFF
1	0	1	1	0	OFF	OFF	OFF	OFF	ON	OFF	OFF	OFF
1	0	0	1	0	OFF	OFF	OFF	OFF	OFF	ON	OFF	OFF
1	0	1	0	0	OFF	OFF	OFF	OFF	OFF	OFF	ON	OFF
1	0	0	0	0	OFF	OFF	OFF	OFF	OFF	OFF	OFF	ON
X[2]	1	0	0	0	OFF	OFF	OFF	OFF	OFF	OFF	OFF	OFF

Notes:
1. LS has an internal 1 MΩ pull-up resistor to logic high. To generate a logic 0, connect LS to GND externally. Leaving LS floating generates a logic 1.
2. LS = don't care, V4 = 1, V3 = V2 = V1 = 0, all ports are terminated to provide an all-isolated state.

Power derating curve

The power derating curve in Figure 2 shows the P1dB compression, P0.1dB compression, maximum RF input power (pulsed), maximum RF input power (CW), absolute maximum RF terminated power (CW), and maximum RF terminated power (CW).

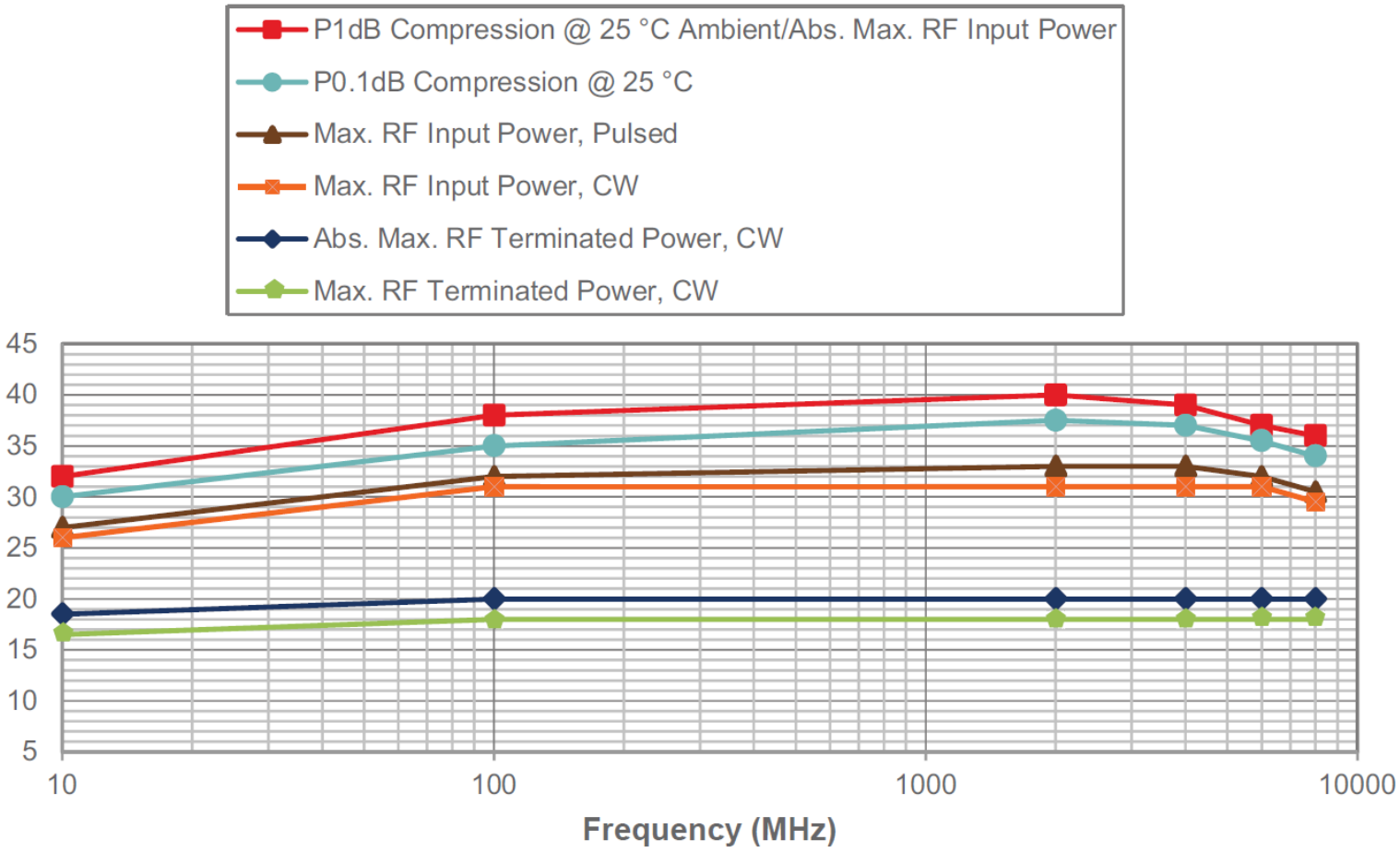


Figure 2 • Power derating curve, 10 MHz–8 GHz, –55 °C to +125 °C ambient, 50Ω

Isolation matrix

Table 6 lists the PE426482 RFC-to-port isolation and Table 7 lists the port-to-port isolation at +25 °C and V_{DD} = 3.3V (Z_S = Z_L = 50Ω).

Table 6. RFC-to-port isolation

ON port	Frequency	Isolation (dB)							
		RF1	RF2	RF3	RF4	RF5	RF6	RF7	RF8
RF1	10–100 MHz 100 MHz–1 GHz 1–2 GHz 2–4 GHz 4–6 GHz 6–8 GHz	–	69 62 57 48 37 34	68 53 48 40 35 31	85 62 56 49 44 41	91 74 68 63 55 56	88 66 60 54 50 47	87 64 58 52 46 45	79 57 51 45 42 38
RF2	10–100 MHz 100 MHz–1 GHz 1–2 GHz 2–4 GHz 4–6 GHz 6–8 GHz	67 52 46 39 32 30	–	69 60 57 49 43 37	90 67 62 54 49 46	91 74 68 63 56 55	88 66 60 53 50 47	86 64 57 52 46 46	77 56 50 45 42 40
RF3	10–100 MHz 100 MHz–1 GHz 1–2 GHz 2–4 GHz 4–6 GHz 6–8 GHz	65 47 42 36 33 31	68 55 51 44 40 36	–	86 66 57 50 42 39	91 74 68 63 56 55	88 66 60 53 49 46	85 63 57 52 47 47	77 55 50 45 42 40
RF4	10–100 MHz 100 MHz–1 GHz 1–2 GHz 2–4 GHz 4–6 GHz 6–8 GHz	65 47 41 36 33 32	67 53 47 41 36 34	68 56 51 44 38 34	–	90 75 69 63 55 50	89 66 59 53 49 47	85 63 57 51 46 47	76 55 49 44 41 40
RF5	10–100 MHz 100 MHz–1 GHz 1–2 GHz 2–4 GHz 4–6 GHz 6–8 GHz	73 51 45 40 37 34	84 61 56 49 45 43	89 65 59 52 48 46	90 75 68 61 56 51	–	68 57 52 45 39 34	68 53 48 41 36 35	66 49 44 38 35 34
RF6	10–100 MHz 100 MHz–1 GHz 1–2 GHz 2–4 GHz 4–6 GHz 6–8 GHz	73 51 45 40 37 34	84 62 56 49 46 44	88 65 59 53 49 45	93 73 67 61 57 55	85 64 56 48 41 38	–	68 56 51 46 38 37	66 50 45 39 35 33
RF7	10–100 MHz 100 MHz–1 GHz 1–2 GHz 2–4 GHz 4–6 GHz 6–8 GHz	73 51 45 40 37 34	84 62 56 49 45 43	89 65 59 53 49 46	92 73 67 61 57 56	88 68 63 56 50 47	69 60 57 50 41 38	–	68 57 52 44 33 33

RF8	10–100 MHz 100 MHz–1 GHz 1–2 GHz 2–4 GHz 4–6 GHz 6–8 GHz	74 52 46 40 37 33	84 62 57 49 46 42	87 66 60 53 49 46	93 73 67 60 57 55	85 63 57 50 46 42	68 54 48 41 35 31	69 65 60 51 34 35	–

Table 7. Port-to-port isolation

ON port	Frequency	Isolation (dB)							
		RF1	RF2	RF3	RF4	RF5	RF6	RF7	RF8
RF1	10–100 MHz	–	65	67	84	91	89	89	88
	100 MHz–1 GHz		47	51	59	75	69	71	64
	1–2 GHz		41	45	53	70	63	65	60
	2–4 GHz		35	39	47	64	57	60	53
	4–6 GHz		31	34	43	57	52	47	45
	6–8 GHz		29	30	40	57	49	47	43
RF2	10–100 MHz	65	–	64	78	90	91	92	89
	100 MHz–1 GHz	46		45	55	75	70	75	74
	1–2 GHz	41		39	49	69	64	69	72
	2–4 GHz	35		34	43	65	58	64	63
	4–6 GHz	32		30	41	57	53	50	51
	6–8 GHz	29		27	38	58	50	50	51
RF3	10–100 MHz	67	65	–	69	94	90	92	91
	100 MHz–1 GHz	51	47		47	75	70	78	80
	1–2 GHz	46	41		41	70	64	72	79
	2–4 GHz	40	36		36	65	58	66	68
	4–6 GHz	37	33		33	57	53	51	54
	6–8 GHz	33	30		30	57	50	51	54
RF4	10–100 MHz	68	67	63	–	90	89	89	91
	100 MHz–1 GHz	53	52	44		71	69	78	79
	1–2 GHz	47	46	39		66	64	71	80
	2–4 GHz	42	41	33		61	58	65	68
	4–6 GHz	38	36	30		54	53	50	54
	6–8 GHz	34	35	28		55	50	50	54
RF5	10–100 MHz	88	91	89	90	–	63	67	68
	100 MHz–1 GHz	79	80	70	71		44	52	52
	1–2 GHz	66	73	64	66		39	46	46
	2–4 GHz	57	66	58	61		33	41	40
	4–6 GHz	50	52	53	55		30	36	36
	6–8 GHz	47	53	51	56		28	35	33
RF6	10–100 MHz	90	92	89	91	69	–	65	67
	100 MHz–1 GHz	77	82	70	75	46		47	51
	1–2 GHz	65	75	65	70	41		42	45
	2–4 GHz	56	66	58	64	35		36	39
	4–6 GHz	49	52	53	59	33		32	35
	6–8 GHz	46	53	50	57	30		31	32
RF7	10–100 MHz	92	92	89	90	78	64	–	64
	100 MHz–1 GHz	85	77	70	76	55	45		45
	1–2 GHz	70	72	64	71	50	39		40
	2–4 GHz	57	64	58	65	44	34		35
	4–6 GHz	48	52	53	59	40	30		29
	6–8 GHz	46	51	50	57	39	27		30
RF8	10–100 MHz	87	91	88	90	82	67	65	–
	100 MHz–1 GHz	69	73	69	75	59	51	47	
	1–2 GHz	67	67	63	70	54	45	41	
	2–4 GHz	56	61	57	64	47	39	35	
	4–6 GHz	46	49	52	59	43	34	29	
	6–8 GHz	42	49	49	56	41	30	29	

Typical performance data

Figures 3–20 show the PE426482 typical performance data at +25 °C and V_{DD} = 3.3V (Z_S = Z_L = 50Ω), unless otherwise specified.

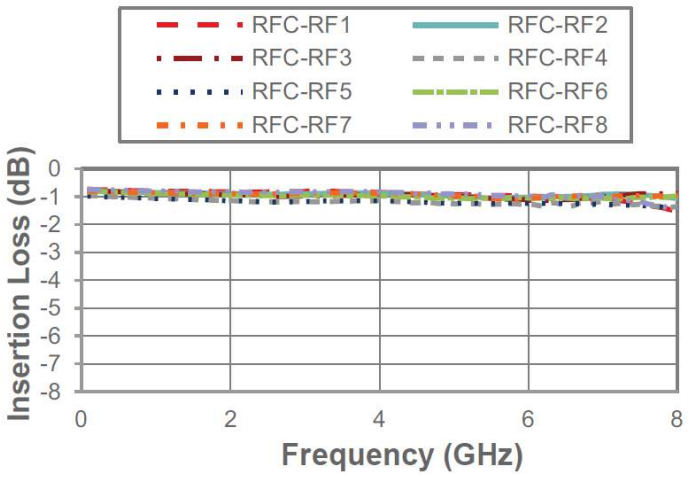


Figure 3. Insertion loss vs. frequency, RFC–RFx

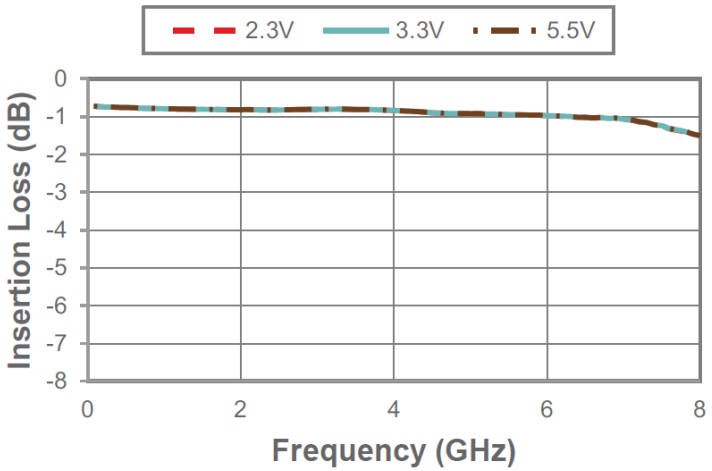


Figure 4. Insertion loss vs. frequency over V_{DD}, RFC–RF1

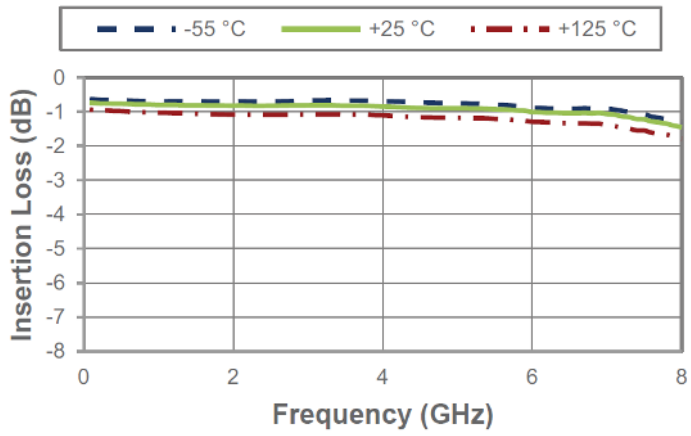


Figure 5. Insertion loss vs. frequency over temperature, RFC–RF1

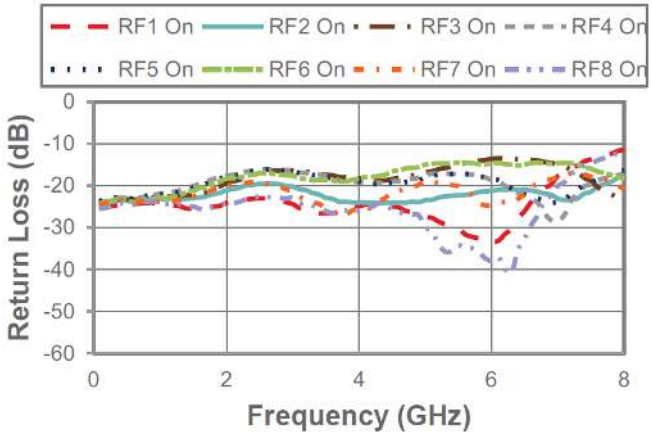


Figure 6. RFC port return loss vs. frequency

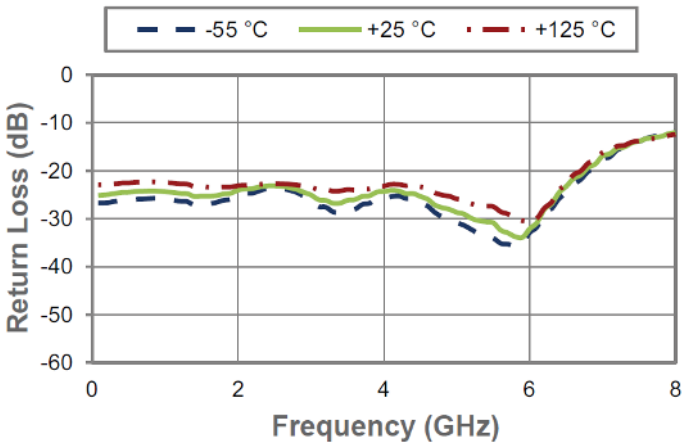


Figure 7. RFC port return loss vs. frequency over temperature, RF1 on

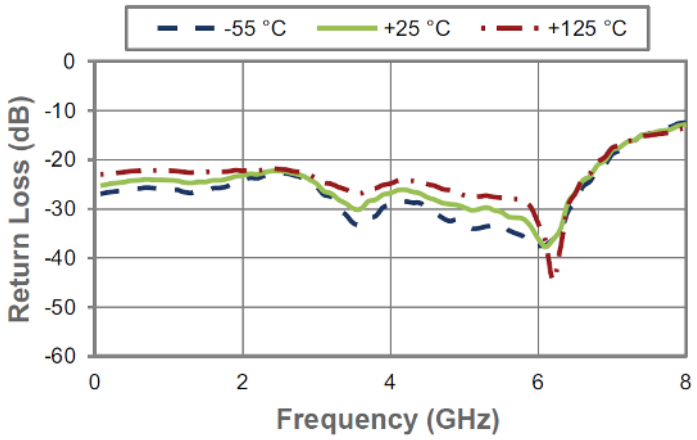


Figure 8. RF1 active port return loss vs. frequency over temperature

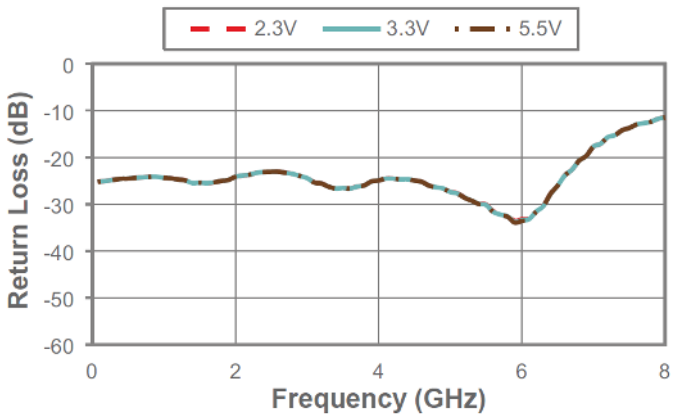


Figure 9. RFC port return loss vs. frequency over V_{DD}, RF1 on

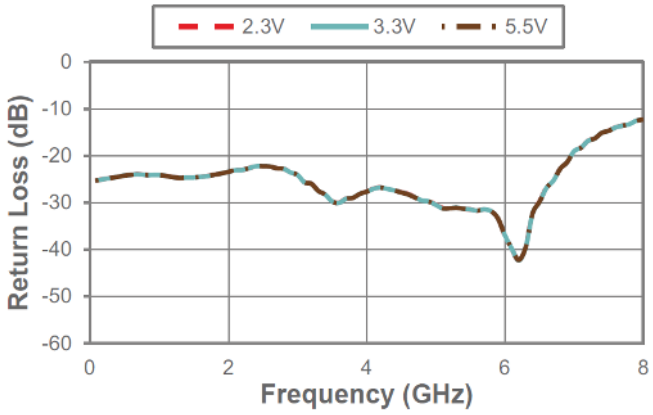


Figure 10. RF1 active port return loss vs. frequency over V_{DD}

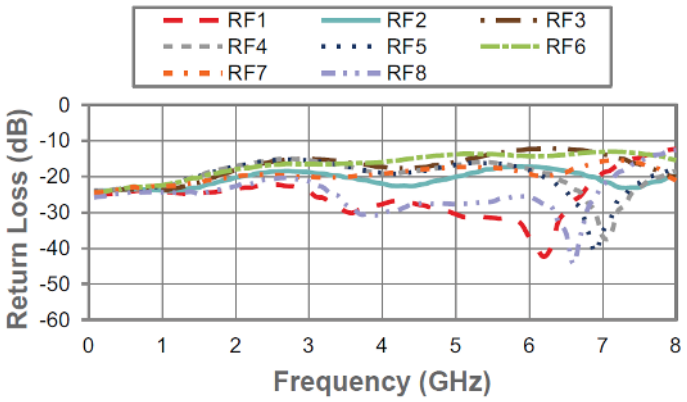


Figure 11. Active port return loss vs. frequency

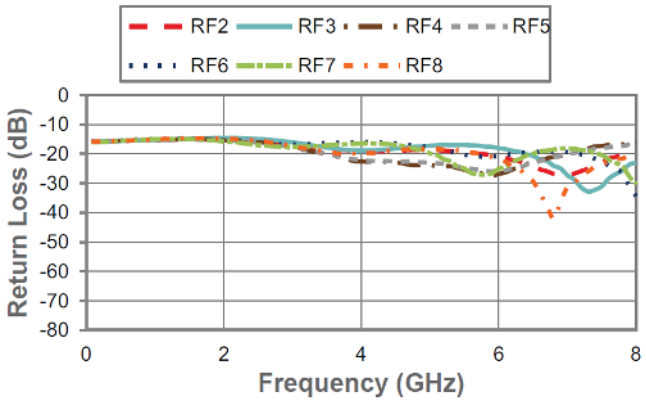


Figure 12. Terminated port return loss vs. frequency, RF1 on

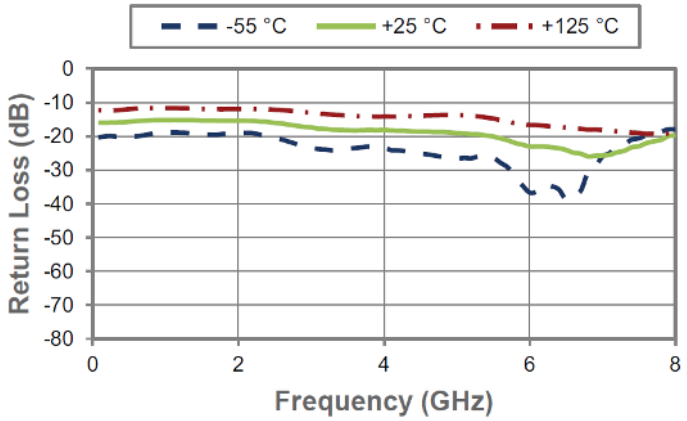


Figure 13. RF2 terminated port return loss vs. frequency over temperature, RF1 on

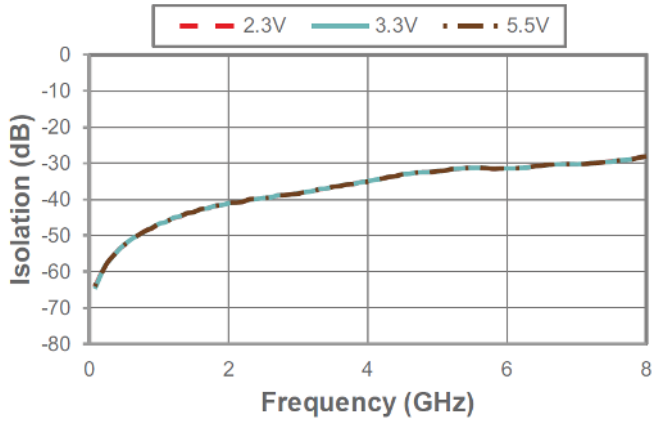


Figure 14. Isolation vs. frequency over V_{DD}, RF1–RF2, RF1 on

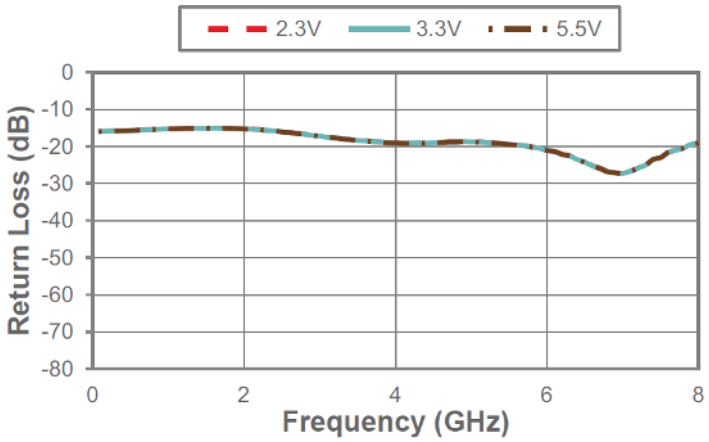


Figure 15. RF2 terminated port return loss vs. frequency over V_{DD}, RF1 on)

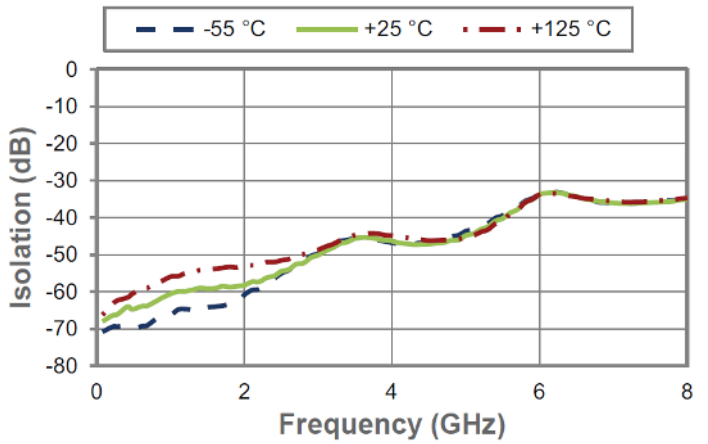


Figure 16. Isolation vs. frequency over temperature, RFC–RF2, RF1 on

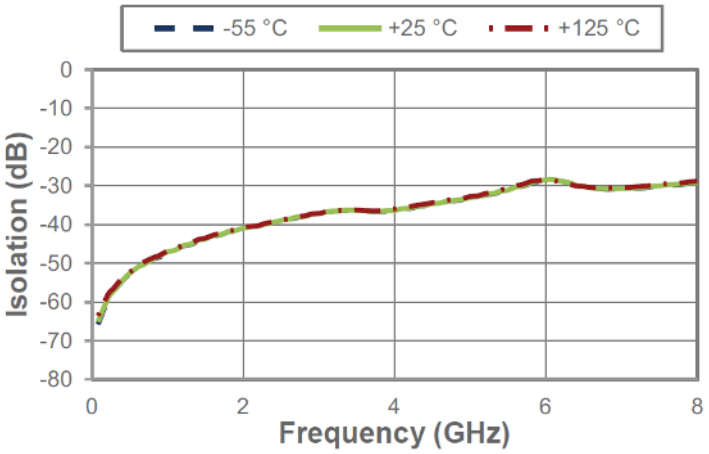


Figure 17. Isolation vs. frequency over temperature, RF1–RF2, RF1 on

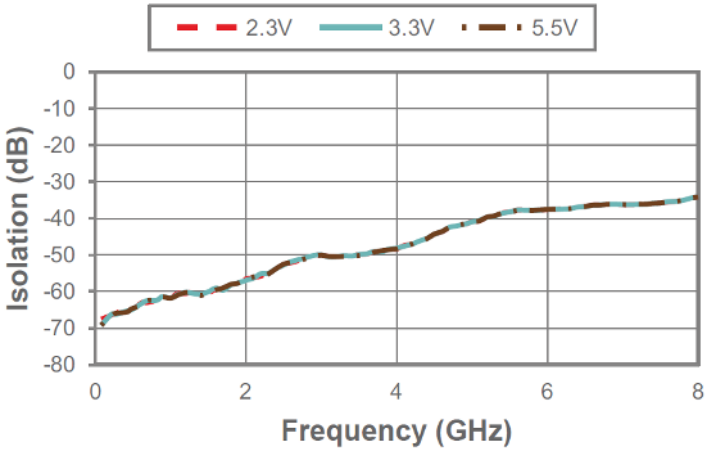


Figure 18. Isolation vs. frequency over V_{DD}, RFC–RF2, RF1 on

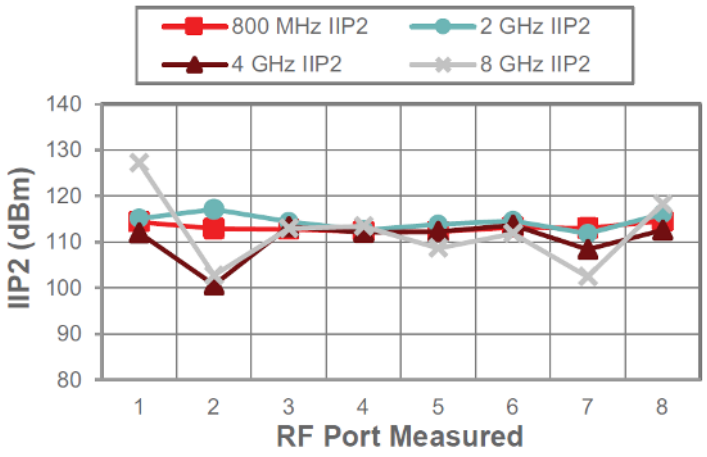


Figure 19. IIP2 vs. RF port measured

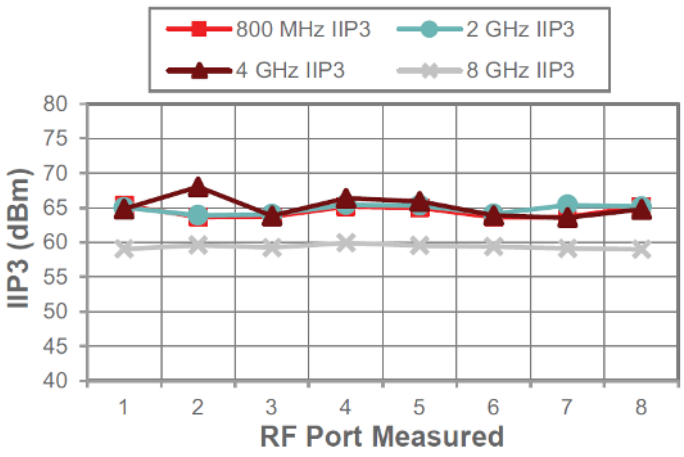


Figure 20. IIP3 vs. RF port measured

Evaluation kit

The high-throw count RF switch evaluation kit (EVK) includes hardware required to control and evaluate the functionality of the

Pin configuration

Figure 22 shows the pin configuration for the 24-lead 4 × 4 × 0.85 mm QFN package, and Table 8 lists the description for each pin.

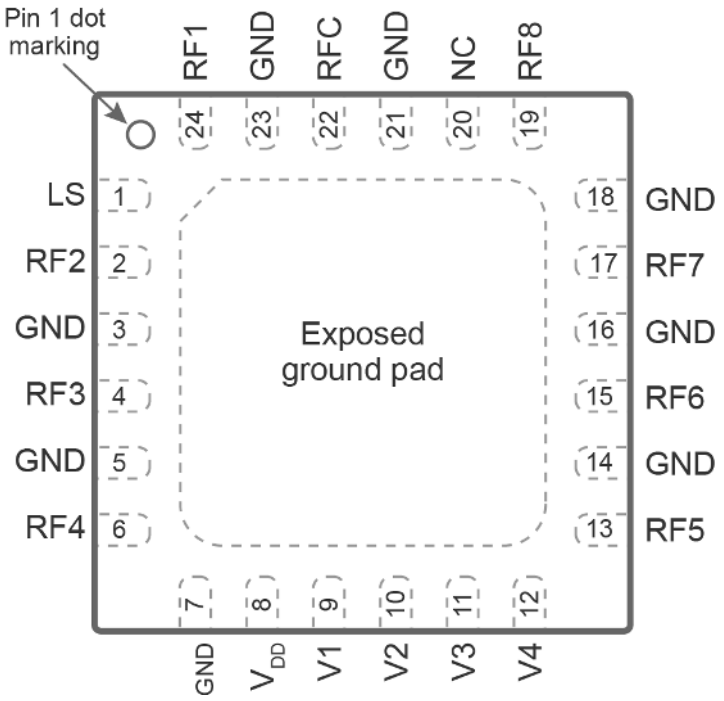


Figure 22. Pin configuration, top view

Table 8. PE426482 pin descriptions

Pin no.	Pin name	Description
1	LS	Logic Select. Determines the definitions for the V1, V2, V3, and V4 pins.
2(1)	RF2	RF port 2
3, 5, 7, 14, 16, 18, 21, 23	GND	Ground
4(1)	RF3	RF port 3
6(1)	RF4	RF port 4
8	VDD	Supply voltage (nominal 3.3V)
9	V1	Digital control logic input 1
10	V2	Digital control logic input 2
11	V3	Digital control logic input 3
12	V4	Digital control logic input 4
13(1)	RF5	RF port 5
15(1)	RF6	RF port 6
17(1)	RF7	RF port 7
19(1)	RF8	RF port 8
20(2)	NC	No connect
22(1)	RFC	RF common port
24(1)	RF1	RF port 1
Pad	GND	Exposed pad. Ground for proper operation.

Notes:
1. RF pins 2, 4, 6, 13, 15, 17, 19, 22, and 24 must be at 0 VDC. These RF pins do not require DC blocking capacitors if the 0 VDC condition is met.
2. Pin 20 (NC) can be connected to GND or left not connected externally.

Packaging information

This section provides the following information:

- Moisture sensitivity level
- Package drawing
- Package marking
- Tape and reel information

Moisture sensitivity level

The PE426482 moisture sensitivity level rating for the 24-lead 4 × 4 × 0.85 mm QFN package is MSL1.

Package drawing

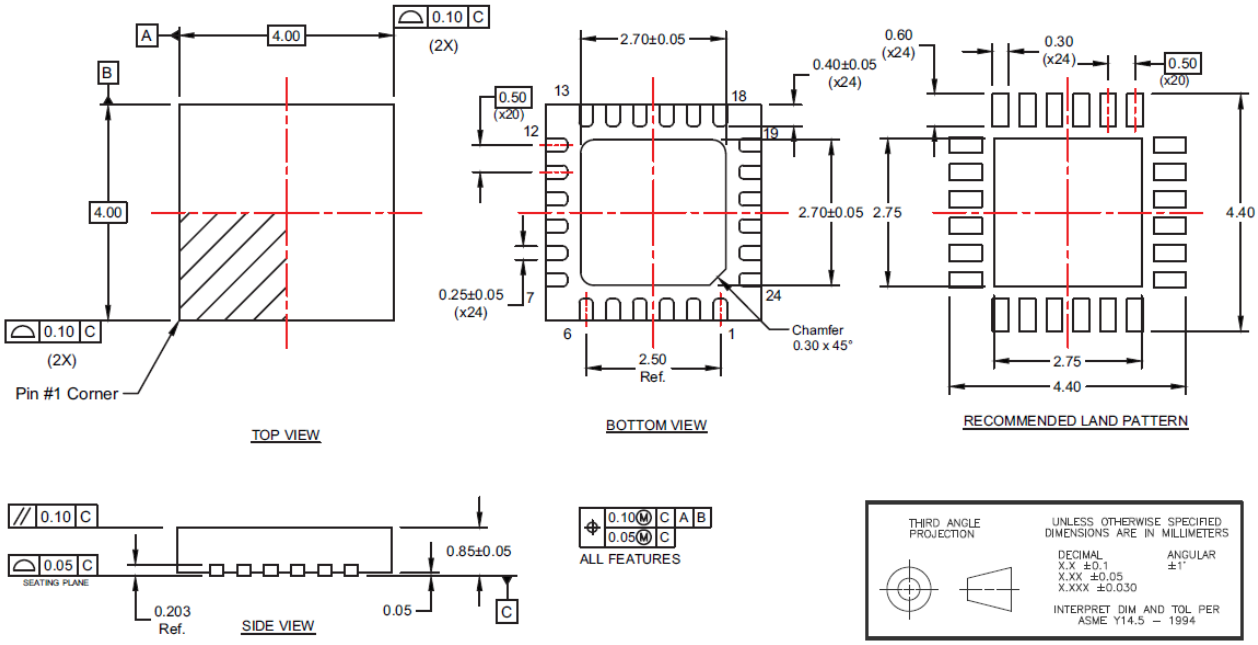


Figure 23. Package drawing for the 24-lead 4 × 4 × 0.85 mm QFN package

Top-marking specification

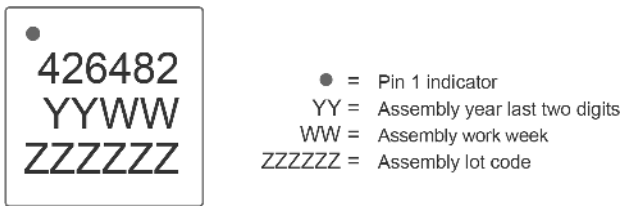
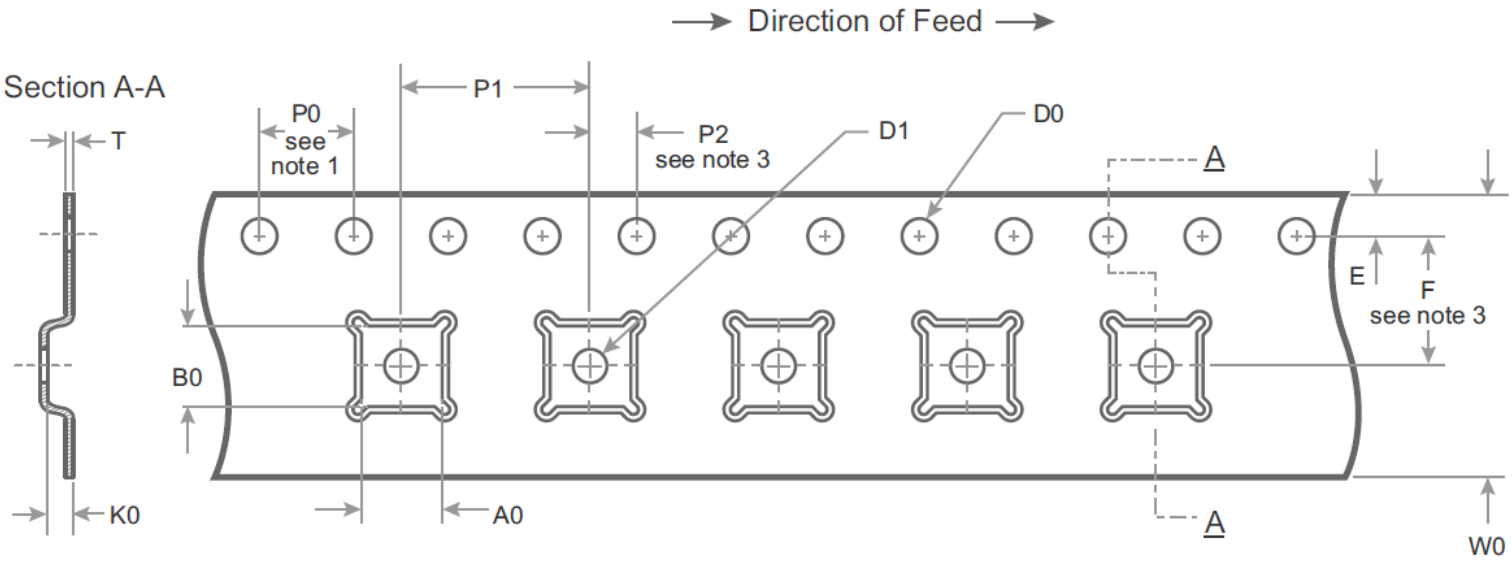


Figure 24. Package marking specification

Tape and reel specification

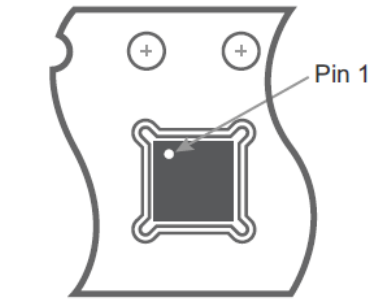


A0	4.35
B0	4.35
K0	1.10
D0	1.50 + 0.10/ -0.00
D1	1.50 min
E	1.75 ± 0.10
F	5.50 ± 0.05
P0	4.00
P1	8.00
P2	2.00 ± 0.05
T	0.30 ± 0.05
W0	12.00 ± 0.30

Notes:

1. 10 Sprocket hole pitch cumulative tolerance ±0.2
2. Camber in compliance with EIA 481
3. Pocket position relative to sprocket hole measured as true position of pocket, not pocket hole

Dimensions are in millimeters unless otherwise specified



Device Orientation in Tape

Figure 25. Tape and reel specification for the 24-lead 4 × 4 × 0.85 mm QFN package

Ordering information

Order code	Description	Packaging	Shipping method
PE426482A-X	PE426482 SP8T RF switch	Green 24-lead 4 × 4 mm QFN	500 units/tape & reel
EK426482-02	PE426482 evaluation Kit	Evaluation kit	1/box

Copyright, patents, and trademark